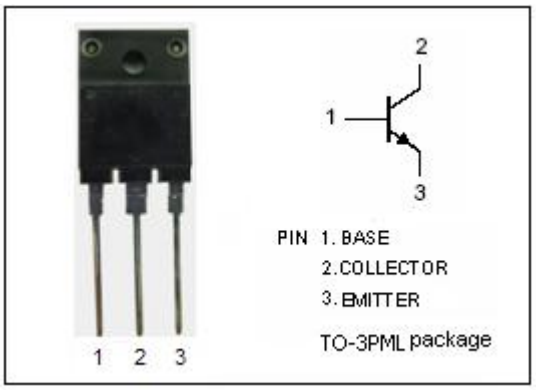
isc Silicon NPN Power Transistor — BU4508AX



DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 800V (Min)
- High-voltage high-speed switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

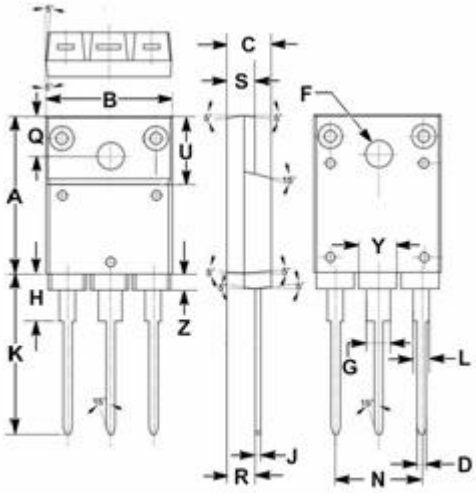
APPLICATIONS

- Designed for use in horizontal deflection circuits of CTV receivers and p.c monitors.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage(V_{BE}= 0)	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current- Continuous	8	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current- Continuous	4	A
I_{BM}	Base Current-Peak	6	A
P_C	Collector Power Dissipation @ T_C=25℃	45	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.8	℃/W



DIM	mm MIN	MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ; I_B= 0	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 1.25A			3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 1.25A			1.03	V
I_{CES}	Collector Cutoff Current	V_{CE}= 1500V ; V_{BE}= 0 V_{CE}= 1500V ; V_{BE}= 0; T_C=125℃			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}=6V ; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 0.1A ; V_{CE}= 5V		12		
h_{FE-2}	DC Current Gain	I_C= 5A ; V_{CE}= 5V	4.2		7.3	
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1MHz		80		pF